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(54) **ORGANIC FIELD EFFECT TRANSISTOR WITH AN ORGANIC DIELECTRIC**

(75) Inventors: **Janos Veres**, Manchester (GB); **Simon Dominic Ogier**, Manchester (GB); **Soad Mohialdin-Khaffaf**, Manchester (GB); **Stephen William Leeming**, Manchester (GB)

(73) Assignee: **Merck Patent GmbH**, Darmstadt (DE)

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(58) **Field of Classification Search** ..... None
See application file for complete search history.

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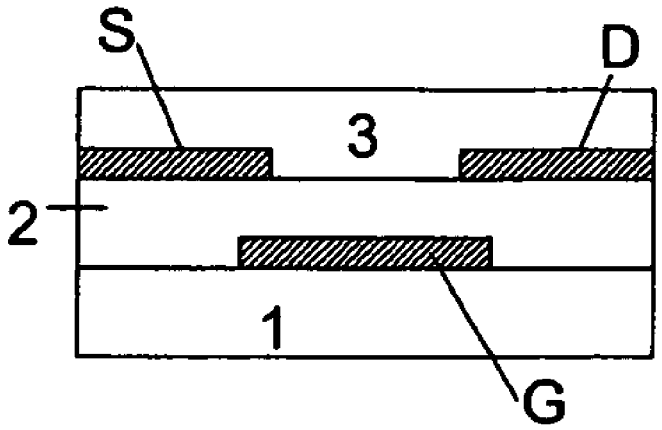
Primary Examiner—Ngân V. Ngô
(74) *Attorney, Agent, or Firm*—Morgan, Lewis & Bockius LLP

(57) **ABSTRACT**

A process of manufacturing an organic field effect device is provided comprising the steps of (a) depositing from a solution an organic semiconductor layer; and (b) depositing from a solution a layer of low permittivity insulating material forming at least a part of a gate insulator, such that the low permittivity insulating material is in contact with the organic semiconductor layer, wherein the low permittivity insulating material is of relative permittivity from 1.1 to below 3.0. In addition, an organic field effect device manufactured by the process is provided.

35 Claims, 3 Drawing Sheets